Hrishikesh Das

List of Publications by Year
in descending order

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18	54	2682572 2	2550090 3
papers	citations	h-index	g-index

18	18	18	24
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Is there a perfect SiC MosFETs Device on an imperfect crystal?. , 2021, , .		6
2	(Invited) Detection of Dislocations Using X-Ray Diffraction Imaging (Topography) KOH Etching and Their Evolution after Epitaxial Growth in 4H-SiC. ECS Transactions, 2021, 104, 141-146.	0.5	0
3	(Invited) Detection of Dislocations Using X-Ray Diffraction Imaging (Topography) KOH Etching and Their Evolution after Epitaxial Growth in 4H-SiC. ECS Meeting Abstracts, 2021, MA2021-02, 1005-1005.	0.0	0
4	(Invited) P-Type and N-Type Channeling Ion Implantation of SiC and Implications for Device Design and Fabrication. ECS Transactions, 2020, 98, 119-124.	0.5	3
5	(Invited) P-Type and N-Type Channeling Ion Implantation of SiC and Implications for Device Design and Fabrication. ECS Meeting Abstracts, 2020, MA2020-02, 1839-1839.	0.0	0
6	(Invited) Influence of Wafering, CMP and Subsurface Damage on Epitaxial Defects and Surface Quality in SiC. ECS Meeting Abstracts, 2019, , .	0.0	0
7	(Invited) Characterization of UV Excitation Accelerated Material Changes on as-Grown SiC Epitaxial Layers and Their Impact on Defect Detection. ECS Transactions, 2018, 86, 69-74.	0.5	1
8	Non-destructive Detection of Screw Dislocations and the Corresponding Defects Nucleated from Them During SiC Epitaxial Growth and Their Effect on Device Characteristics. Journal of Electronic Materials, 2018, 47, 5099-5104.	2.2	0
9	(Invited) Characterization of UV Excitation Accelerated Material Changes on As-Grown SiC Epitaxial Layers and Their Impact on Defect Detection. ECS Meeting Abstracts, 2018, , .	0.0	0
10	Characterization of Leakage Causing Visible Epitaxial Defects Nucleating from Crystal Defects in the Substrate. ECS Transactions, 2016, 75, 233-237.	0.5	6
11	(Invited) Enabling SiC Yield and Reliability through Epitaxy and Characterization. ECS Transactions, 2015, 69, 29-32.	0.5	5
12	Detection of Crystal Defects in High Doped Epitaxial Layers and Substrates by Photoluminescence. Materials Science Forum, 0, 897, 222-225.	0.3	5
13	Evaluation of the Effect of Ultraviolet Light Excitation during Characterization of Silicon Carbide Epitaxial Layers. Materials Science Forum, 0, 924, 261-264.	0.3	2
14	Effect of Defects in Silicon Carbide Epitaxial Layers on Yield and Reliability. Materials Science Forum, 0, 963, 284-287.	0.3	11
15	Statistical Analysis of Killer and Non-Killer Defects in SiC and the Impacts to Device Performance. Materials Science Forum, 0, 1004, 458-463.	0.3	11
16	A Deeper Look into the Effects of Extended Defects in SiC Epitaxial Layers on Device Performance and Reliability. Materials Science Forum, 0, 1062, 406-410.	0.3	1
17	SiC Diode with Vertical Superjunction Realized Using Channeled Implant and Multi-Step Epitaxial Growth. Materials Science Forum, 0, 1062, 549-553.	0.3	1
18	Pulsed Forward Bias Body Diode Stress of 1700 V SiC MOSFETs with Individual Mapping of Basal Plane Dislocations. Materials Science Forum, 0, 1062, 554-559.	0.3	2